# TLVH431 family

# Low voltage adjustable precision shunt regulators Rev. 1 — 27 April 2012 Produ

Product data sheet

#### 1. **General description**

Low voltage three-terminal shunt regulator family with an output voltage range between V<sub>ref</sub> (1.24 V) and 18 V, to be set by two external resistors.

Table 1. **Product overview** 

Reference voltage	Package	Temperature range	Pinning configuration		
tolerance (V <sub>ref</sub> )		0 °C to 70 °C	–40 °C to 85 °C	–40 °C to 125 °C	(see <u>Table 5</u> )
1.5 %	SOT23	TLVH431CDBZR	TLVH431IDBZR	TLVH431QDBZR	normal pinning
		-	-	TLVH431MQDBZR	mirrored pinning
	SOT753	-	-	TLVH431QDBVR	-
1 %	SOT23	TLVH431ACDBZR	TLVH431AIDBZR	TLVH431AQDBZR	normal pinning
		-	-	TLVH431AMQDBZR	mirrored pinning
	SOT753	-	-	TLVH431AQDBVR	-
0.75 %	SOT23	-	-	TLVH431DQDBZR	normal pinning
				TLVH431DMQDBZR	mirrored pinning
	SOT753	-	-	TLVH431DQDBVR	-

#### **Features and benefits** 2.

Programmable output voltage up to 18 V

■ Three different reference voltage tolerances:

◆ Standard grade: 1.5 %

◆ A-Grade: 1 % ◆ D-Grade: 0.75 %

■ Typical temperature drift: 4 mV (in a range of -40 °C up to 125 °C)

Low output noise

**Typical output impedance: 0.1 Ω** 

Sink current capability: 0.08 mA to 70 mA

AEC-Q100 qualified (grade 1)

# 3. Applications

- Shunt regulator
- Precision current limiter
- Precision constant current sink
- Isolated feedback loop for Switch Mode Power Supply (SMPS)



# 4. Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{KA}$	cathode-anode voltage		$V_{ref}$	-	18	V
I <sub>K</sub>	cathode current		0.08	-	70	mΑ
$V_{ref}$	reference voltage	$V_{KA} = V_{ref}$ ; $I_K = 10$ mA; $T_{amb} = 25$ °C				
	Standard-Grade (1.5 %)		1222	1240	1258	mV
	A-Grade (1 %)		1228	1240	1252	mV
	D-Grade (0.75 %)		1231	1240	1249	mV

# 5. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TLVH431CDBZR	TO-236AB	plastic surface-mounted package; 3 leads	SOT23
TLVH431IDBZR			
TLVH431QDBZR			
TLVH431MQDBZR			
TLVH431ACDBZR			
TLVH431AIDBZR			
TLVH431AQDBZR			
TLVH431AMQDBZR			
TLVH431DQDBZR			
TLVH431DMQDBZR			
TLVH431QDBVR	SC-74A	plastic surface-mounted package; 5 leads	SOT753
TLVH431AQDBVR			
TLVH431DQDBVR			

# 6. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>	Type number	Marking code[1]
TLVH431CDBZR	NM*	TLVH431AMQDBZR	NX*
TLVH431IDBZR	NN*	TLVH431DQDBZR	*SE
TLVH431QDBZR	NP*	TLVH431DMQDBZR	*SF
TLVH431MQDBZR	NW*	TLVH431QDBVR	AB3
TLVH431ACDBZR	NQ*	TLVH431AQDBVR	AB6
TLVH431AIDBZR	NR*	TLVH431DQDBVR	AC1
TLVH431AQDBZR	NS*	-	-

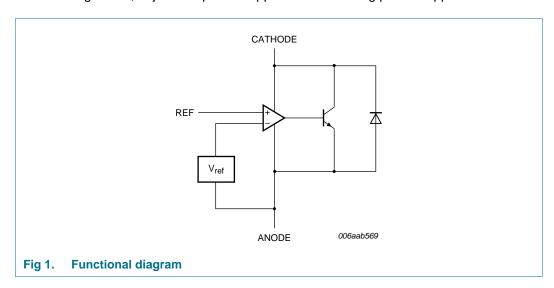
<sup>[1] \* =</sup> placeholder for manufacturing site code.

TLVH431\_FAM

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# 7. Functional diagram

The TLVH431 family comprises a range of 3-terminal adjustable shunt regulators, with specified thermal stability over applicable automotive and commercial temperature ranges. The output voltage can be set to any value between  $V_{ref}$  (approximately 1.24 V) and 18 V with two external resistors (see Figure 10). These devices have a typical output impedance of 0.1  $\Omega$ . Active output circuitry provides a very sharp turn-on characteristic, making these devices excellent replacements for Zener diodes in many applications like on-board regulation, adjustable power supplies and switching power supplies.



# 8. Pinning information

Table 5.	Pinning							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
SOT23; normal pinning: All types without MQDBZR ending								
1	REF	reference		DEE				
2	k	cathode	3	REF				
3	а	anode	1 2	a k				
SOT23; r	mirrored pini	ning: All types with MQ	DBZR ending					
1	k	cathode		DEE				
2	REF	reference	3	REF				
3	а	anode	1 7 72	a — k				

 Table 5.
 Pinning ...continued

Pin	Symbol	Description	S	implified outline	Graphic symbol
SOT753					
1	n.c.	not connected	<u>[1]</u>		REF
2	n.c.	not connected	<u>[1]</u>	5	KEF
3	k	cathode			a — k
4	REF	reference		1 2 3	006aab355
5	а	anode			

<sup>[1]</sup> Pin 1 and 2 can be connected to anode for better thermal performance.

# 9. Limiting values

Table 6. Limiting values

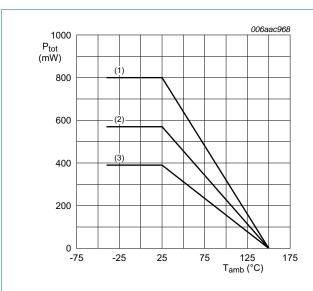
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{KA}$	cathode-anode voltage		-	20	V
I <sub>K</sub>	cathode current		-25	80	mA
I <sub>ref</sub>	reference current		-0.05	3	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT23		<u>[1]</u> _	390	mW
			[2] _	570	mW
			[3]	800	mW
	SOT753		<u>[1]</u> -	310	mW
			[2] _	460	mW
			[3]	700	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature				
	TLVH431XCDBZR		0	+70	°C
	TLVH431XIDBZR		-40	+85	°C
	TLVH431XQDBZR		-40	+125	°C
	TLVH431XQDBVR				
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

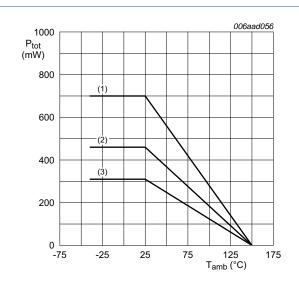
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode 1 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for anode 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 2. SOT23: Power derating curves



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for anode 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 3. SOT753: Power derating curves

Table 7. ESD maximum ratings  $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{ESD}$	electrostatic discharge voltage	MIL-STD-883 (human body model)	-	4	kV
		machine model	-	400	V

# 10. Recommended operating conditions

Table 8. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{KA}$	cathode-anode voltage		$V_{ref}$	18	V
$I_{K}$	cathode current		0.08	70	mA

# 11. Thermal characteristics

Table 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
_	raiailletei	Conditions	IVIIII	тур	IVIAX	Oilit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT23		<u>[1]</u> _	-	320	K/W
			[2] _	-	220	K/W
			[3]	-	155	K/W
	SOT753		<u>[1]</u> _	-	400	K/W
			[2] _	-	270	K/W
			[3]	-	180	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[4]			
	SOT23		-	-	35	K/W
	SOT753		-	-	40	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode 1 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[4]</sup> Soldering point of anode.

# 12. Characteristics

Table 10. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

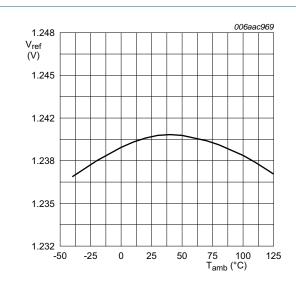
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Standard-0	Grade (1.5 %): TLVH431CDB	ZR; TLVH431IDBZR; TLVH4310	QDBZR; TLVH	1431MQDBF	RZ; TLVH431	QDBVR
$V_{ref}$	reference voltage	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
		T <sub>amb</sub> = 25 °C	1222	1240	1258	mV
	TLVH431CDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	1210	-	1270	mV
	TLVH431IDBZR	$T_{amb} = -40  ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$	1202	-	1278	mV
	TLVH431QDBZR TLVH431MQDBRZ TLVH431QDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	1194	-	1286	mV
$\Delta V_{ref}$	reference voltage variation	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
	TLVH431CDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	-	2	10	mV
	TLVH431IDBZR	$T_{amb} = -40  ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$	-	3	10	mV
	TLVH431QDBZR TLVH431MQDBRZ TLVH431QDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	-	4	10	mV
$\Delta V_{ref} / \Delta V_{KA}$	reference voltage variation to cathode-anode voltage variation ratio	$I_K = 10 \text{ mA};$ $\Delta V_{KA} = V_{ref} \text{ to } 18 \text{ V}$	-	-0.5	-1.5	mV/V
I <sub>ref</sub>	reference current	$I_K$ = 10 mA; R1 = 10 kΩ; R2 = open	-	0.19	0.30	μΑ
$\Delta I_{ref}$	reference current variation	$I_K = 10 \text{ mA};$ R1 = 10 kΩ; R2 = open				
	TLVH431CDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	-	0.03	0.10	μΑ
	TLVH431IDBZR	$T_{amb} = -40  ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$	-	0.06	0.16	μΑ
	TLVH431QDBZR TLVH431MQDBRZ TLVH431QDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	-	0.07	0.24	μΑ
I <sub>K(min)</sub>	minimum cathode current	$V_{KA} = V_{ref}$	-	55	80	μΑ
I <sub>off</sub>	off-state current	$V_{KA} = 18 \text{ V}; V_{ref} = 0$	-	0.01	0.05	μΑ
Z <sub>KA</sub>	dynamic cathode-anode impedance	$I_K = 0.1$ mA to 70 mA; $V_{KA} = V_{ref}$ ; f < 1 kHz				
	SOT23		-	0.10	0.15	Ω
	SOT753		-	0.15	0.20	Ω

Table 10. Characteristics ... continued  $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
A-Grade (1	%): TLVH431ACDBZR; TLV	H431AIDBZR; TLVH431AQDBZ	ZR; TLVH431	AMQDBZR;	TLVH431AQ	DBVR
V <sub>ref</sub>	reference voltage	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
		T <sub>amb</sub> = 25 °C	1228	1240	1252	mV
	TLVH431ACDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	1221	-	1259	mV
	TLVH431AIDBZR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 85  ^{\circ}\text{C}$	1215	-	1265	mV
	TLVH431AQDBZR TLVH431AMQDBRZ TLVH431AQDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	1209	-	1271	mV
$\Delta V_{ref}$	reference voltage variation	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
	TLVH431ACDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	-	2	10	mV
	TLVH431AIDBZR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 85  ^{\circ}\text{C}$	-	3	10	mV
	TLVH431AQDBZR TLVH431AMQDBRZ TLVH431AQDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	-	4	10	mV
$\Delta V_{ref} / \Delta V_{KA}$	reference voltage variation to cathode-anode voltage variation ratio	$I_K = 10 \text{ mA};$ $\Delta V_{KA} = V_{ref} \text{ to } 18 \text{ V}$	-	-0.5	<b>−1.5</b>	mV/V
I <sub>ref</sub>	reference current	$I_K = 10 \text{ mA};$ R1 = 10 kΩ; R2 = open	-	0.19	0.30	μΑ
$\Delta I_{ref}$	reference current variation	$I_K$ = 10 mA; R1 = 10 kΩ; R2 = open				
	TLVH431ACDBZR	$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	-	0.03	0.10	μΑ
	TLVH431AIDBZR	$T_{amb} = -40  ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$	-	0.06	0.16	μΑ
	TLVH431AQDBZR TLVH431AMQDBRZ TLVH431AQDBVR	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	-	0.07	0.24	μА
I <sub>K(min)</sub>	minimum cathode current	$V_{KA} = V_{ref}$	-	55	80	μΑ
I <sub>off</sub>	off-state current	$V_{KA} = 18 \text{ V}; V_{ref} = 0$	-	0.01	0.05	μΑ
Z <sub>KA</sub>	dynamic cathode-anode impedance	$I_K = 0.1$ mA to 70 mA; $V_{KA} = V_{ref}$ ; f < 1 kHz				
	SOT23		-	0.10	0.15	Ω
	SOT753		-	0.15	0.20	Ω

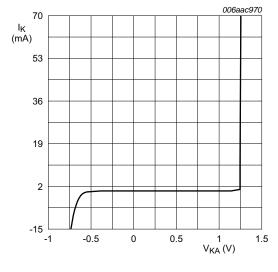
Table 10. Characteristics ... continued  $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
D-Grade (0	).75 %): TLVH431DQDBZR; 1	TLVH431DMQDBZR; TLVH431D	QDBVR			
$V_{ref}$	reference voltage	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
		T <sub>amb</sub> = 25 °C	1231	1240	1249	mV
		$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 125  ^{\circ}\text{C}$	1215	-	1265	mV
$\Delta V_{ref}$	reference voltage variation	$V_{KA} = V_{ref}$ ; $I_K = 10 \text{ mA}$				
		$T_{amb} = 0  ^{\circ}C$ to 70 $^{\circ}C$	-	2	10	mV
		$T_{amb} = -40  ^{\circ}\text{C} \text{ to } 85  ^{\circ}\text{C}$	-	3	10	mV
		$T_{amb}$ = -40 °C to 125 °C	-	4	10	mV
$\Delta V_{ref} / \Delta V_{KA}$	reference voltage variation to cathode-anode voltage variation ratio	$I_K = 10 \text{ mA};$ $\Delta V_{KA} = V_{ref} \text{ to } 18 \text{ V}$	-	-0.5	<b>−1.5</b>	mV/V
I <sub>ref</sub>	reference current	$I_K = 10 \text{ mA};$ R1 = 10 k $\Omega$ ; R2 = open	-	0.19	0.30	μΑ
$\Delta I_{ref}$	reference current variation	$I_K = 10 \text{ mA};$ R1 = 10 k $\Omega$ ; R2 = open; $T_{amb} = -40 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	0.07	0.24	μА
I <sub>K(min)</sub>	minimum cathode current	$V_{KA} = V_{ref}$	-	55	80	μΑ
I <sub>off</sub>	off-state current	$V_{KA} = 18 \text{ V}; V_{ref} = 0$	-	0.01	0.05	μΑ
Z <sub>KA</sub>	dynamic cathode-anode impedance	$I_K = 0.1$ mA to 70 mA; $V_{KA} = V_{ref}$ ; f < 1 kHz				
	SOT23		-	0.10	0.15	Ω
	SOT753		-	0.15	0.20	Ω



I<sub>K</sub> = 10 mA; V<sub>KA</sub> = V<sub>ref</sub>

Fig 4. Reference voltage as a function of ambient temperature; typical values



 $V_{KA} = V_{ref}; T_{amb} = 25 \, ^{\circ}C$ 

Fig 5. Cathode current as a function of cathode-anode voltage; typical values

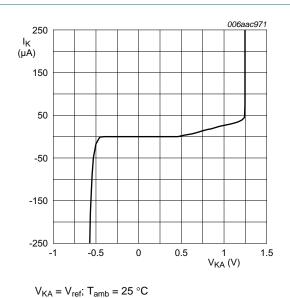
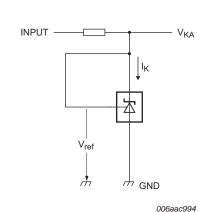
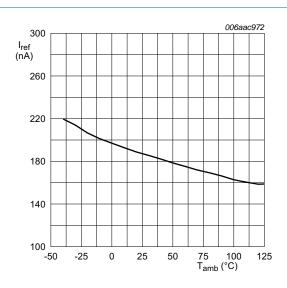


Fig 6. Cathode current as a function of cathode-anode voltage; typical values



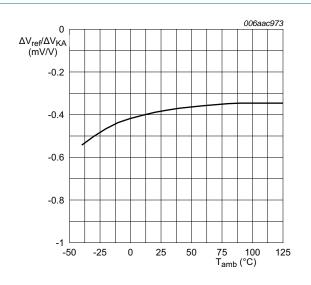
 $I_K = 10 \text{ mA}; V_{KA} = V_{ref}$ 

Fig 7. Test circuit to Figure 4, 5 and 6



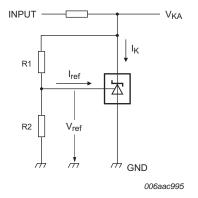
 $V_{KA}$  = 1.24 V;  $I_{K}$  = 10 mA; R1 = 10 k $\Omega$ ; R2 = open

Fig 8. Reference current as a function of ambient temperature; typical values



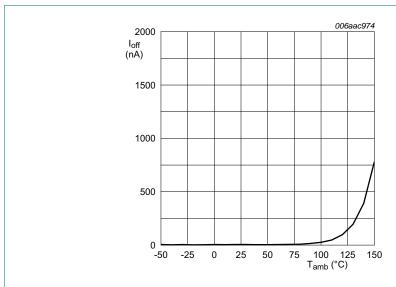
 $I_K = 10$  mA;  $T_{amb} = 25$  °C

Fig 9. Reference voltage variation to cathode-anode voltage variation ratio as a function of ambient temperature; typical values



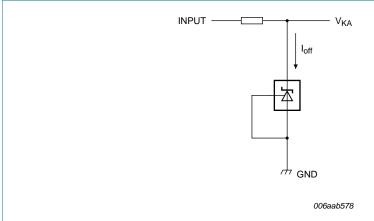
$$V_{KA} = V_{ref} \times \left( 1 + \frac{RI}{R2} \right) + I_{ref} \times RI$$

Fig 10. Test circuit to Figure 8 and 9



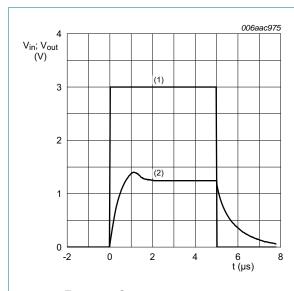
 $V_{KA} = 18 \text{ V}; V_{ref} = 0 \text{ V}$ 

Fig 11. Off-state current as a function of ambient temperature; typical values



 $V_{KA} = 18 \text{ V}; V_{ref} = 0 \text{ V}$ 

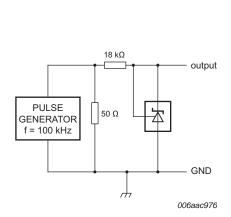
Fig 12. Off-state current as a function of ambient temperature; test circuit



 $T_{amb} = 25 \, ^{\circ}C$ 

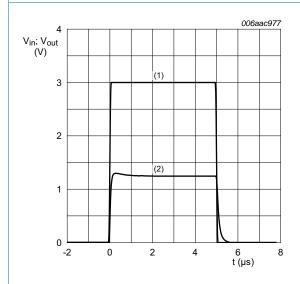
- (1) Input
- (2) Output

Fig 13. Input voltage and output voltage as a function of time; typical values



T<sub>amb</sub> = 25 °C

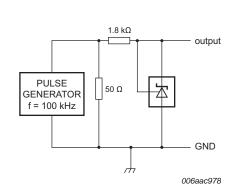
Fig 14. Test circuit to Figure 13



 $T_{amb} = 25 \, ^{\circ}C$ 

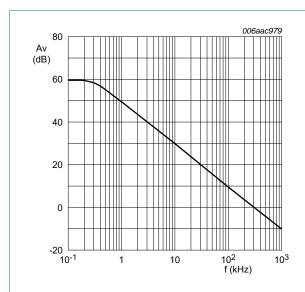
- (1) Input
- (2) Output

Fig 15. Input voltage and output voltage as a function of time; typical values



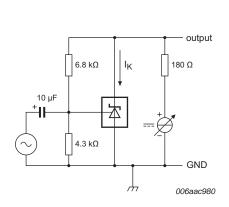
 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 16. Test circuit to Figure 15



 $I_K = 10 \text{ mA}$ ;  $T_{amb} = 25 \, ^{\circ}\text{C}$ 

Fig 17. Voltage amplification as a function of frequency; typical values



 $I_K = 10 \text{ mA}$ ;  $T_{amb} = 25 \, ^{\circ}\text{C}$ 

Fig 18. Test circuit to Figure 17

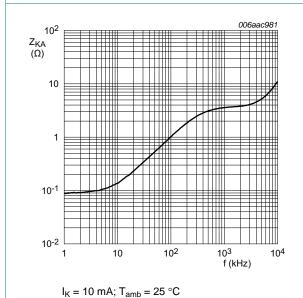
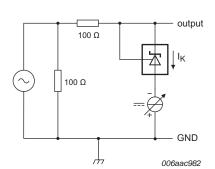
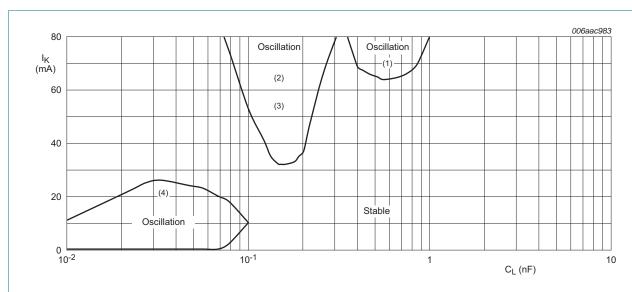


Fig 19. Dynamic cathode-anode impedance as a function of frequency; typical values



 $I_K$  = 10 mA;  $T_{amb}$  = 25 °C

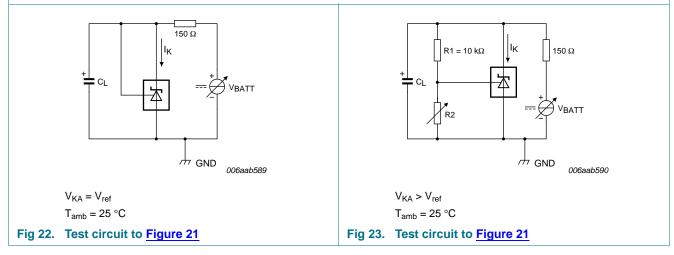
Fig 20. Test circuit to Figure 19



T<sub>amb</sub> = 25 °C

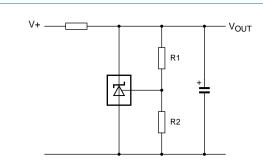
- (1)  $V_{KA} = V_{ref}$
- (2)  $V_{KA} = 2 V$
- (3)  $V_{KA} = 3 V$
- (4)  $V_{KA} = 18 \text{ V}$

Fig 21. Cathode current as a function of load capacitance; typical values



<u>Figure 21, 22</u> and <u>23</u> show the stability boundaries and test circuits for the worst case conditions with a load capacitance mounted as close as possible to the device. The required load capacitance for stable operation varies depending on the operating temperature and capacitor Equivalent Series Resistance (ESR). Verify that the application circuit is stable over the anticipated operating current and temperature ranges.

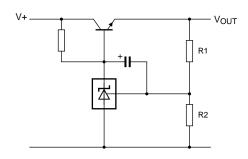
# 13. Application information



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$$V_{OUT} = \left(I + \frac{RI}{R2}\right) \times V_{rej}$$

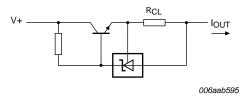
Fig 24. Shunt regulator



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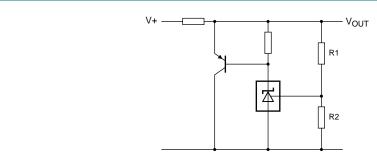
$$V_{OUT} = \left(I + \frac{RI}{R2}\right) \times V_{ref}, V_{OUT(min)} = V_{ref} + V_{be}$$

Fig 25. Series pass regulator



$$I_{OUT} = \frac{V_{ref}}{R_{CL}}$$

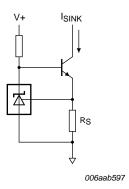
Fig 26. Constant current source



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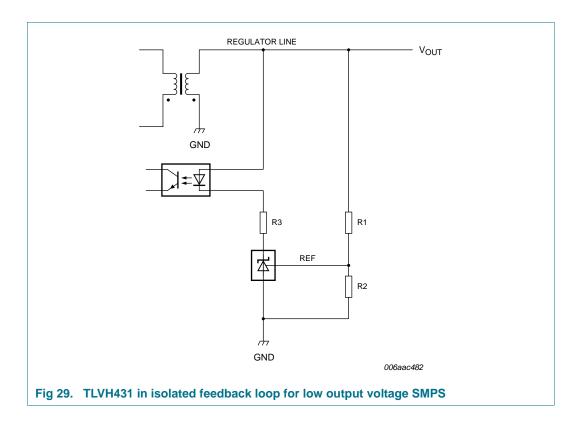
$$V_{OUT} = \left(I + \frac{RI}{R2}\right) \times V_{rej}$$

Fig 27. High-current shunt regulator



 $I_{SINK} = \frac{V_{ref}}{R_S}$ 

Fig 28. Constant current sink

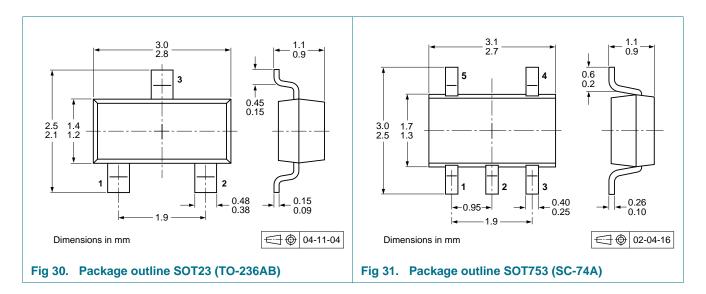


# 14. Test information

### 14.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q100 - Failure mechanism based stress test qualification for integrated circuits*, and is suitable for use in automotive applications.

# 15. Package outline



# 16. Packing information

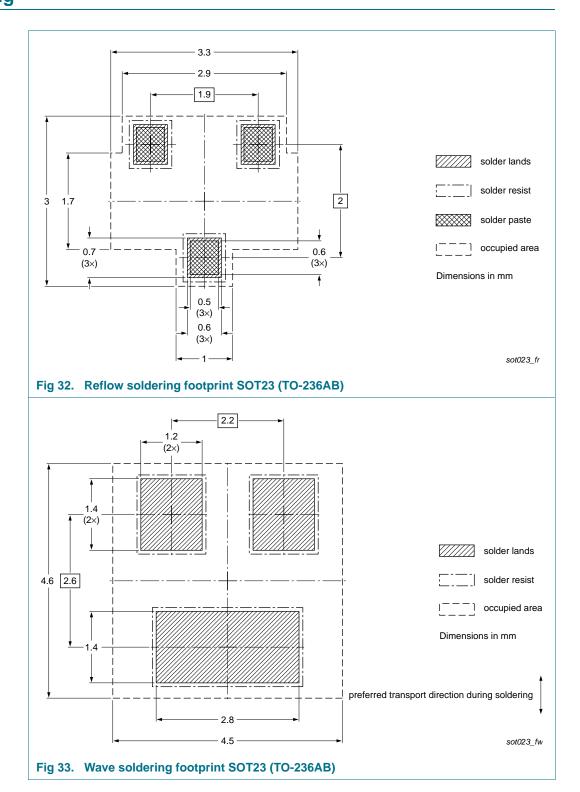
Table 11. Packing methods

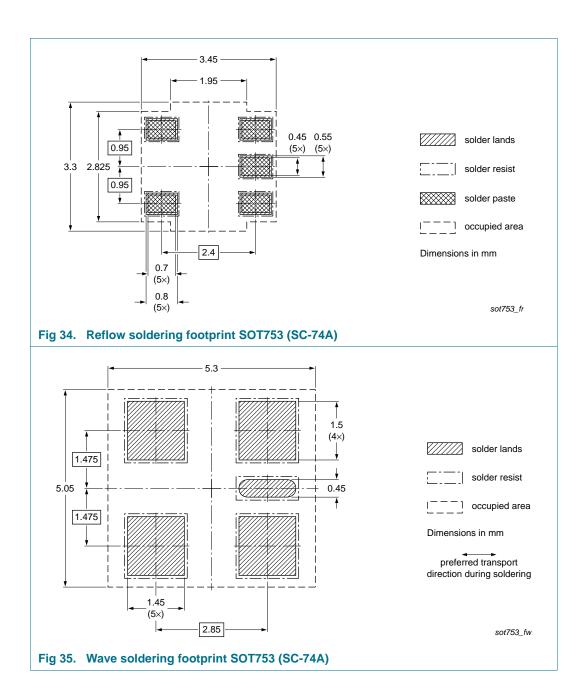
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
			3000	10000	
TLVH431XBZR	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
TLVH431XBVR	SOT753	4 mm pitch, 8 mm tape and reel	-115	-	

<sup>[1]</sup> For further information and the availability of packing methods, see <u>Section 20</u>.

# 17. Soldering







# 18. Revision history

### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TLVH431_FAM v.1	20120427	Product data sheet	-	-

### 19. Legal information

#### 19.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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TLVH431\_FAM

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# **TLVH431 family**

# Low voltage adjustable precision shunt regulators

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